

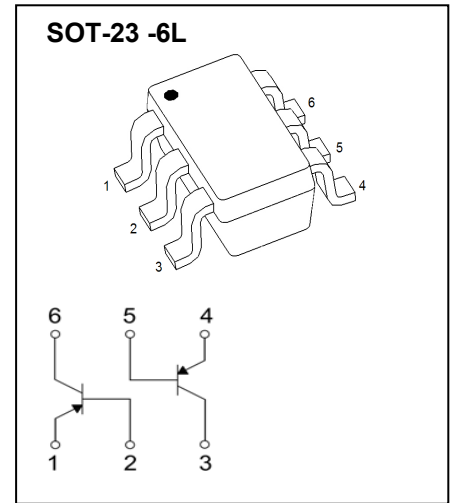
Plastic-Encapsulate Transistors

DUAL TRANSISTOR (PNP+PNP)

FEATURE

Complementary NPN Type available MMDT8050F

MARKING: D2TY



MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-40	V
V_{CEO}	Collector-Emitter Voltage	-25	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current	-0.5	A
P_C	Collector Power Dissipation	300	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	417	$^{\circ}\text{C}/\text{W}$
T_J, T_{stg}	Operation Junction and Storage Temperature Range	-55~+150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100\mu\text{A}, I_E=0$	-40		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1\text{mA}, I_B=0$	-25		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100\mu\text{A}, I_C=0$	-5		V
Collector cut-off current	I_{CBO}	$V_{CB} = -40\text{V}, I_E=0$		-0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE} = -20\text{V}, I_B=0$		-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -3\text{V}, I_C=0$		-0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = -1\text{V}, I_C = -50\text{mA}$	200	350	
	$h_{FE(2)}$	$V_{CE} = -1\text{V}, I_C = -500\text{mA}$	50		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -500\text{mA}, I_B = -50\text{mA}$		-0.6	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -500\text{mA}, I_B = -50\text{mA}$		-1.2	V
Transition frequency	f_T	$V_{CE} = -6\text{V}, I_C = -20\text{mA}$ $f=30\text{MHz}$	150		MHz



Typical Characteristics

